Elektronische Bauelemente

SBAS16

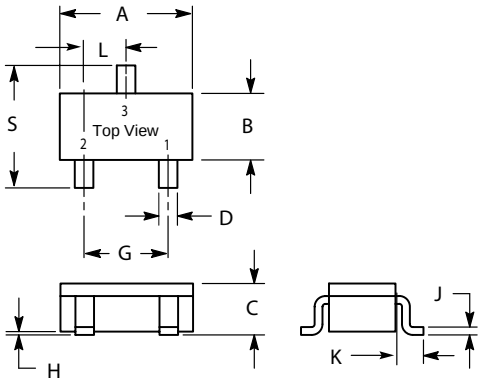
High-Speed Switching Diode

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

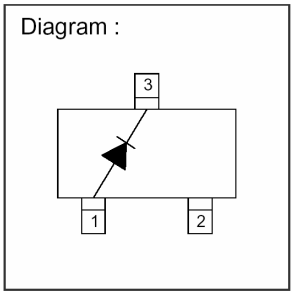
Description

* The SBAS16 is designed for high-speed switching application in hybrid thick and thin-film circuits.
* The devices is manufactured by the silicon epitaxial planar process and packed in a plastic surface mount package.

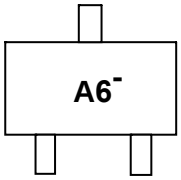


SC-59		
Dim	**Min**	**Max**
A	2.70	3.10
B	1.40	1.60
C	1.00	1.30
D	0.35	0.50
G	1.70	2.10
H	0.00	0.10
J	0.10	0.26
K	0.20	0.60
L	0.85	1.15
S	2.40	2.80
All Dimension in mm		

Diagram :



Marking



Absolute Maximum Ratings at T_A = 25℃

Parameter	Symbol	Ratings	Unit
Reverse Voltage	V_R	75	V
Repetitive Reverse Voltage	V_{RR}	85	V
Forward Current	I_F	250	mA
Repetitive Forward Current	I_{FR}	500	mA
Forward Surge Current (1ms)	I_{FSM}	1000	mW
Total Power Dissipation	P_D	200	mW
Operating Junction and Storage Temperature Range	Tj, Tstg	-65~+150	℃

Characteristics at T_A = 25℃

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)	75	-	V	IR=100uA
Forward Voltage	VF(1)	-	715	mV	IF=1mA
	VF(2)	-	855	mV	IF=10mA
	VF(3)	-	1000	mV	IF=50mA
	VF(4)	-	1250	mV	IF=150mA
Reverse Current	IR	-	1	uA	VR=75V
Total Capacitance	CT		2	pF	VR=0, f=1MHz
Reverse Recovery Time	Trr	-	6	nS	IF=IR=10mA, RL=100Ω measured at IR=1mA

Characteristics Curve